

22. (NEW) The process of claim 20, wherein the ratio of SiH_4 to N_2O is maintained at about 1.22:1.

23. (NEW) The process of claim 18, wherein the interpoly dielectric is silicon nitride.

24. (NEW) The process of claim 18, wherein the removing of the antireflective coating comprises the step of etching with hot phosphoric acid.

25. (NEW) The process of claim 19, wherein the antireflective coating is removed before subjecting the anti-reflective coating to a temperature greater than about 400°C .
